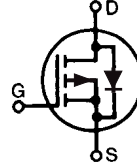


PolarP™
Power MOSFET
IXTH16P60P
IXTT16P60P

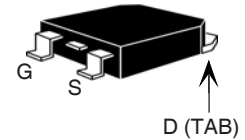
$$V_{DSS} = -600V$$

$$I_{D25} = -16A$$

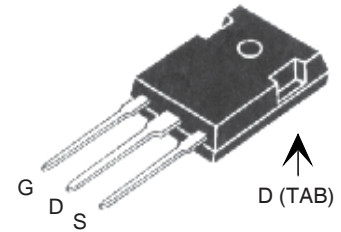
$$R_{DS(on)} \leq 720m\Omega$$

 P-Channel Enhancement Mode
 Avalanche Rated


TO-268 (IXTT)



TO-247 (IXTH)


 G = Gate D = Drain
 S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	- 600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	- 600	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	- 16	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	- 48	A
I_{AR}	$T_C = 25^\circ\text{C}$	- 16	A
E_{AS}	$T_C = 25^\circ\text{C}$	2.5	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	460	W
T_J		- 55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		- 55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-268	5	g
	TO-247	6	g

Features:

- International standard packages
- Avalanche Rated
- Rugged PolarP™ process
- Low package inductance
 - easy to drive and to protect

Applications:

- High side switching
- Push-pull amplifiers
- DC Choppers
- Current regulators
- Automatic test equipment

Advantages:

- Low gate charge results in simple drive requirement
- High power density
- Fast switching
- Easy to parallel

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250\mu A$	- 600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	- 2.5		V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$			- 25 μA
	$V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			- 200 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			720 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = -10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	11	18	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$		5120	pF
C_{oss}			445	pF
C_{rss}			60	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External)		29	ns
t_r			25	ns
$t_{d(off)}$			60	ns
t_f			38	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		92	nC
Q_{gs}			27	nC
Q_{gd}			23	nC
R_{thJC}				0.27°C/W
R_{thCS}		0.21		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			- 16 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			- 64 A
V_{SD}	$I_F = -8\text{A}$, $V_{GS} = 0\text{V}$, Note 1			- 2.8 V
t_{rr}	$I_F = -8\text{A}$, $-di/dt = -150\text{A}/\mu\text{s}$ $V_R = -100\text{V}$, $V_{GS} = 0\text{V}$		440	ns
Q_{RM}			7.4	μC
I_{RM}			- 33.6	A

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

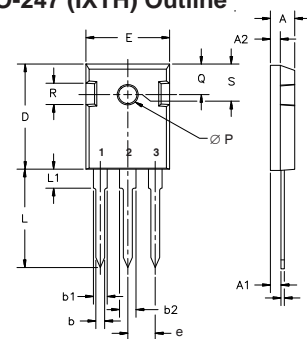
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

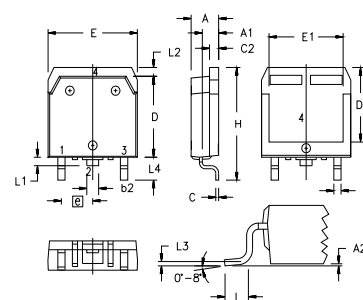
TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

TO-268 (IXTT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @ 25°C

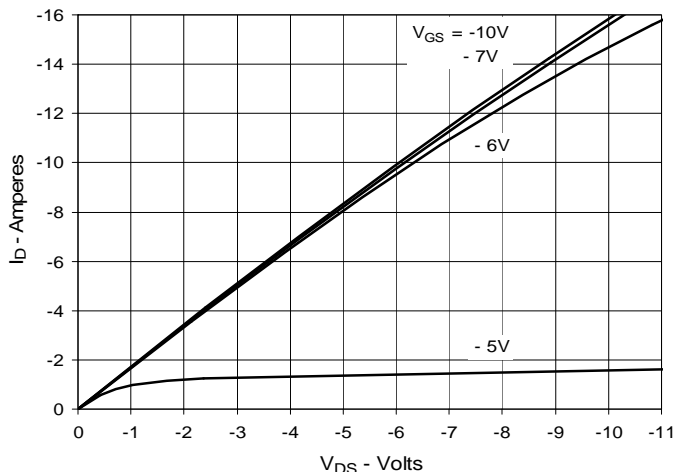


Fig. 2. Extended Output Characteristics @ 25°C

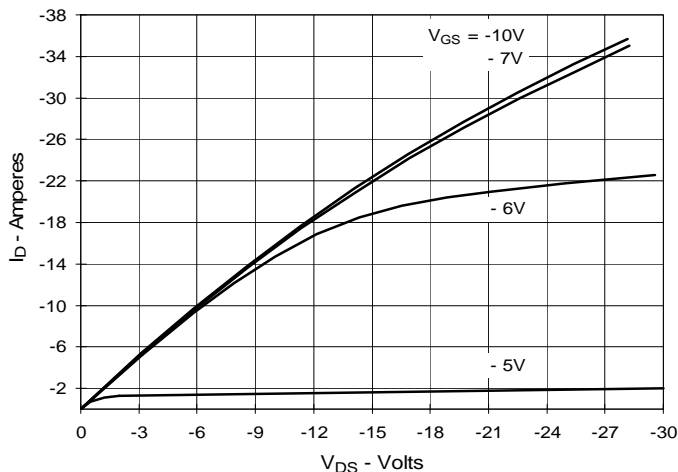


Fig. 3. Output Characteristics @ 125°C

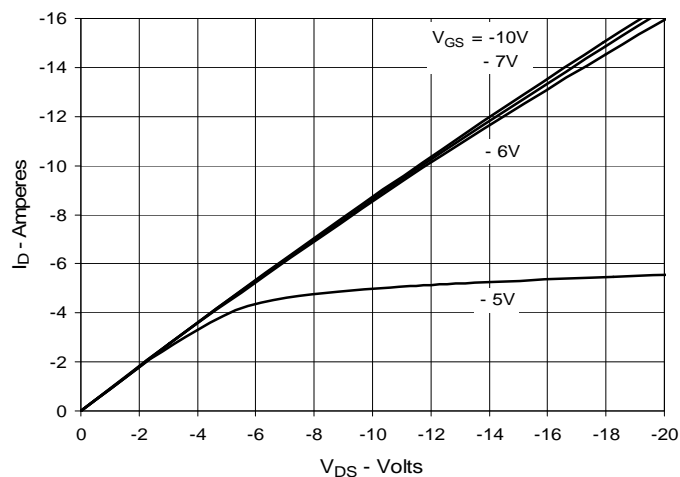


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -8A$ vs. Junction Temperature

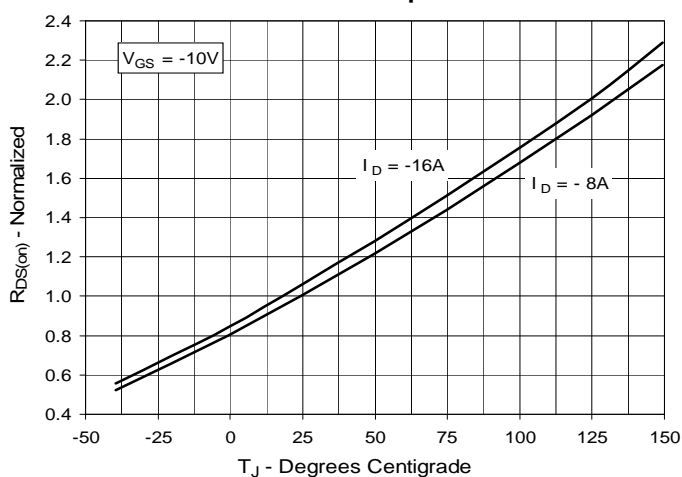


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -8A$ vs. Drain Current

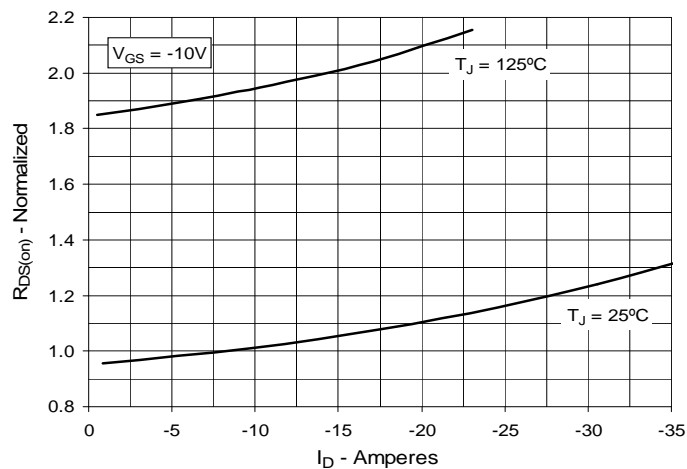


Fig. 6. Maximum Drain Current vs. Case Temperature

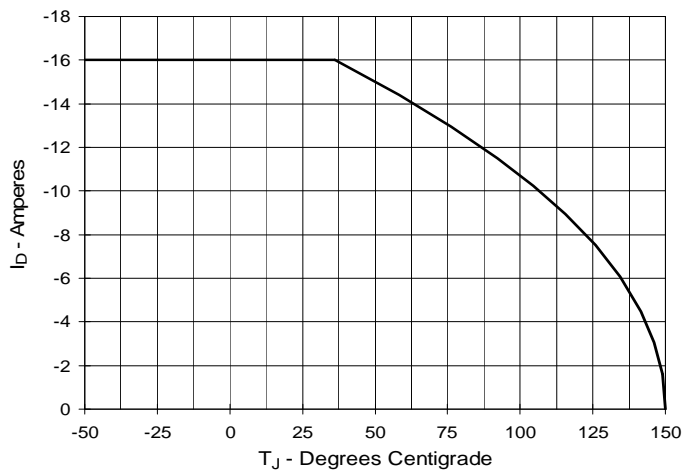


Fig. 7. Input Admittance

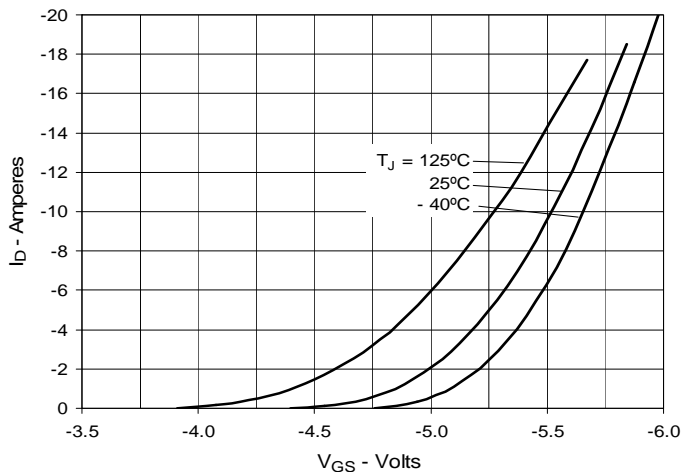


Fig. 8. Transconductance

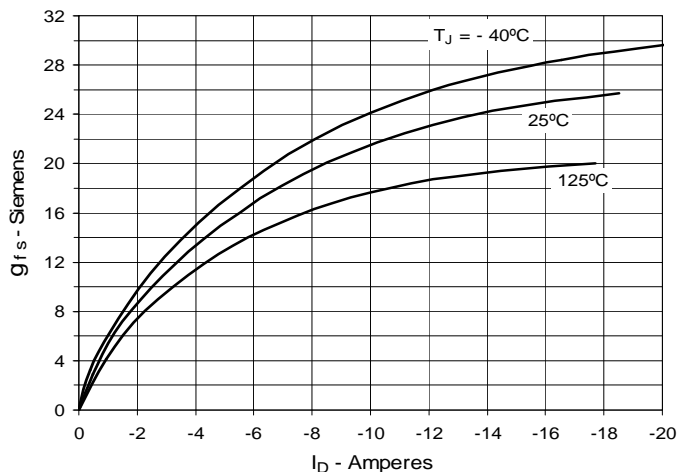


Fig. 9. Forward Voltage Drop of Intrinsic Diode

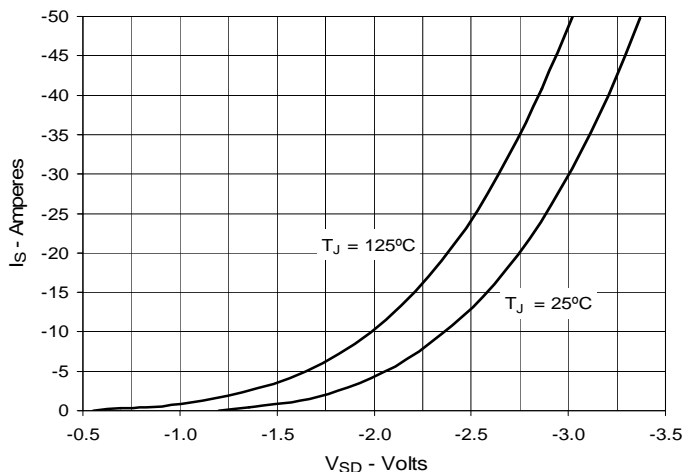


Fig. 10. Gate Charge

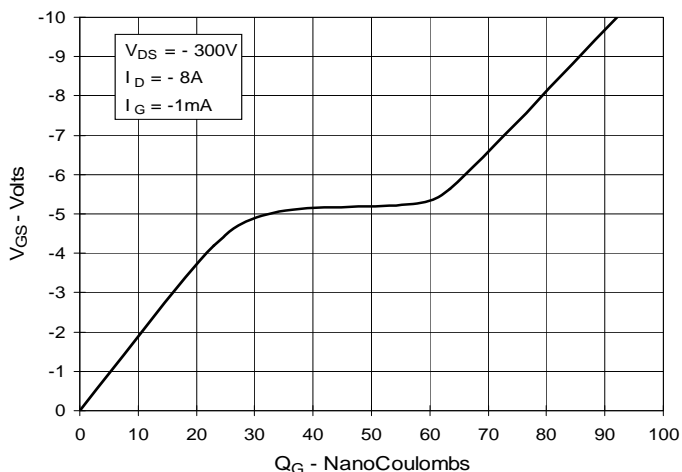


Fig. 11. Capacitance

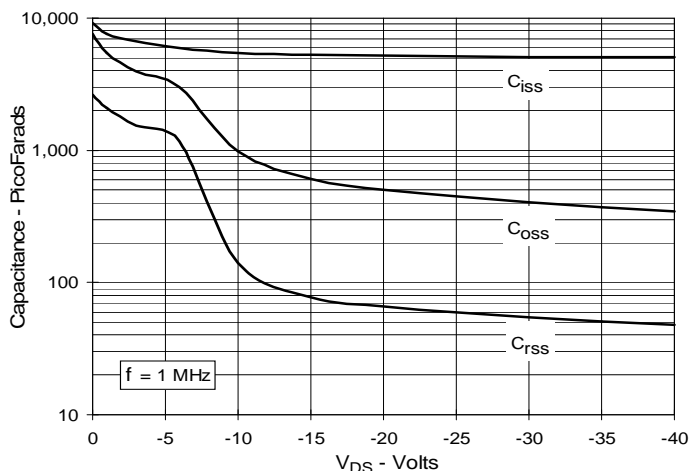
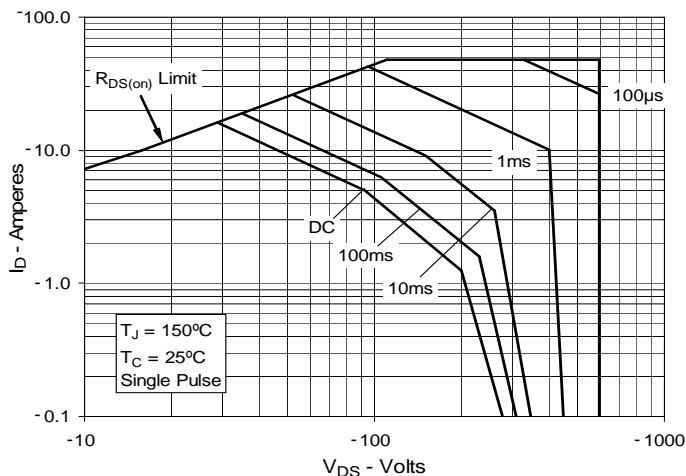


Fig. 12. Forward-Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 13. Maximum Transient Thermal Impedance

